

N-channel 30 V, 4.0 mΩ logic level MOSFET in LFPAK56 using NextPowerS3 Technology

10 October 2013

**Product data sheet** 

### 1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LFPAK56 package. NextPowerS3 portfolio utilising Nexperia's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

### 2. Features and benefits

- Ultra low Q<sub>G</sub>, Q<sub>GD</sub> and Q<sub>OSS</sub> for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1 µA leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Wave solderable; exposed leads for optimal visual solder inspection

### 3. Applications

Table 4

- On-board DC-to-DC solutions for server and telecommunications
- Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control

### 4. Quick reference data

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Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>		-	-	95	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	64	W



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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Tj	junction temperature		-55	-	175	°C
Static chara	acteristics	· · · · ·				
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	4.4	5.5	mΩ
		$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 10	-	3.4	4	mΩ
Dynamic cl	haracteristics	· · · · ·				
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; Fig. 12; Fig. 13	-	2.4	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; Fig. 12; Fig. 13	-	9.1	-	nC
Source-dra	in diode	· · · · ·				
S	softness factor	$I_{S} = 25 \text{ A}; V_{GS} = 0 \text{ V}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$ $V_{DS} = 15 \text{ V}; \underline{\text{Fig. 16}}$	-	1.1	-	

## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G-UF44
4	G	gate	មុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

## 6. Ordering information

Table 3. Ordering information							
Type number Package							
	Name	Description	Version				
PSMN4R0-30YLD	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

### 7. Marking

Table 4. Marking codes			
Type number	1	Marking code	
PSMN4R0-30YLD		4D030L	
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### 8. Limiting values

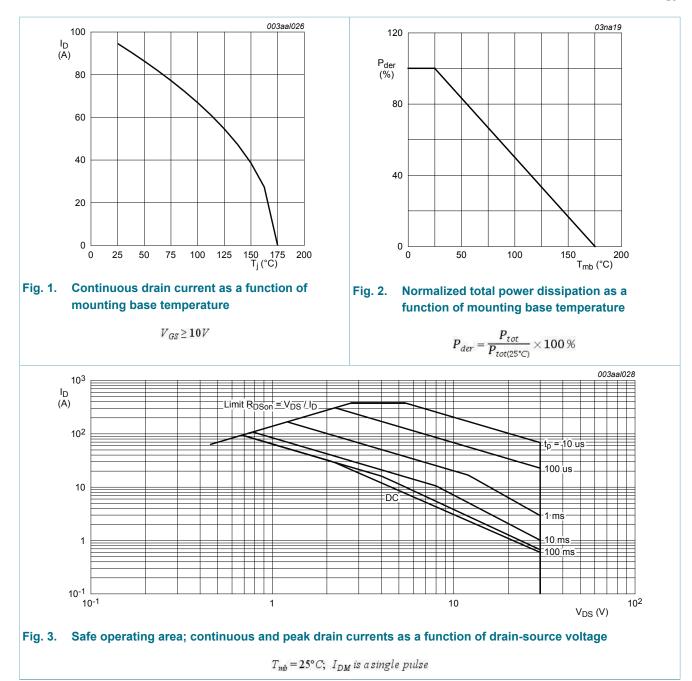
#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	30	V
V <sub>DGR</sub>	drain-gate voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ		-	30	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	95	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 1</u>		-	67	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$ ; Fig. 3		-	378	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	64	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ		375	-	V
Source-drai	n diode	·		1	1	
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	54	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	378	А
Avalanche r	ruggedness	·		1	1	
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 25 A; V <sub>sup</sub> ≤ 30 V; R <sub>GS</sub> = 50 Ω; unclamped; t <sub>p</sub> = 129 µs	[1]	-	63	mJ

[1] Protected by 100% test

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### 9. Thermal characteristics

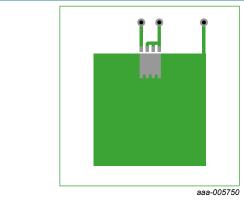
Table 6. T	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 6</u>	-	2.14	2.33	K/W

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	Fig. 4	-	50	-	K/W
from junction to ambient	<u>Fig. 5</u>	-	125	-	K/W	



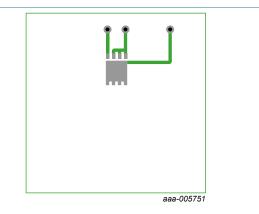


Fig. 4. PCB layout for thermal resistance junction to ambient 1" square pad; FR4 Board; 2oz copper



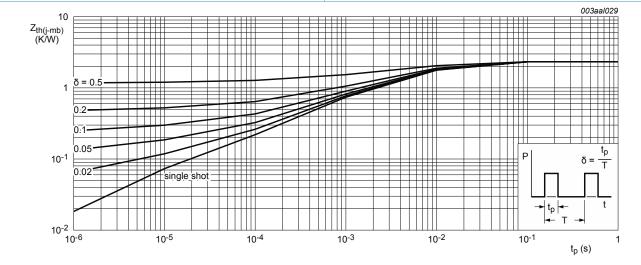


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

### **10. Characteristics**

Fable 7. Characteristics							
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static charac	Static characteristics						
V <sub>(BR)DSS</sub> drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	30	-	-	V		
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	27	-	-	V	
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	1.2	1.74	2.2	V	

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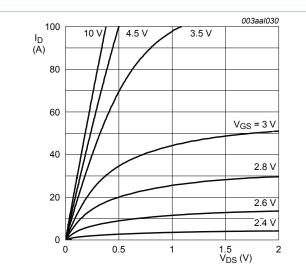
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
ΔV <sub>GS(th)</sub> /ΔT	gate-source threshold voltage variation with temperature	25 °C < T <sub>j</sub> < 150 °C	-	-4.1	-	mV/K
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 24 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 24 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		$V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	4.4	5.5	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; Fig. 11; Fig. 10	-	-	9.1	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 10	-	3.4	4	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; Fig. 11; Fig. 10	-	-	6.6	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	2.2	-	Ω
Dynamic cha	racteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 25 A; $V_{DS}$ = 15 V; $V_{GS}$ = 10 V; Fig. 12; Fig. 13	-	19.4	-	nC
		$I_D$ = 25 A; $V_{DS}$ = 15 V; $V_{GS}$ = 4.5 V; Fig. 12; Fig. 13	-	9.1	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	18.2	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D$ = 25 A; $V_{DS}$ = 15 V; $V_{GS}$ = 4.5 V;	-	2.6	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	1.9	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	0.7	-	nC
Q <sub>GD</sub>	gate-drain charge		-	2.4	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	2.3	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	1272	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	-	812	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	87	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; R <sub>L</sub> = 0.6 Ω; V <sub>GS</sub> = 4.5 V;	-	10.7	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	21.2	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	14.9	-	ns
t <sub>f</sub>	fall time		-	11.7	-	ns

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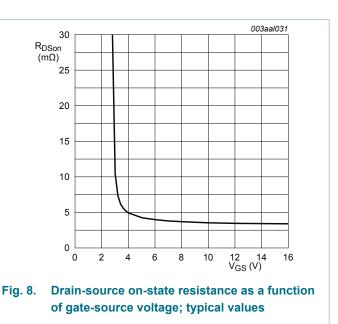
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q <sub>oss</sub>	output charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 15 V; f = 1 MHz; T <sub>j</sub> = 25 °C		-	16	-	nC
Source-dra	in diode	·					
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 15 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 15</u>		-	0.82	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{\rm S}$ = 25 A; dI_{\rm S}/dt = -100 A/µs; V_{\rm GS} = 0 V;		-	25.1	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 15 V; <u>Fig. 16</u>	[1]	-	13.3	-	nC
t <sub>a</sub>	reverse recovery rise time			-	11.9	-	ns
t <sub>b</sub>	reverse recovery fall time			-	13.1	-	ns
S	softness factor	-		-	1.1	-	







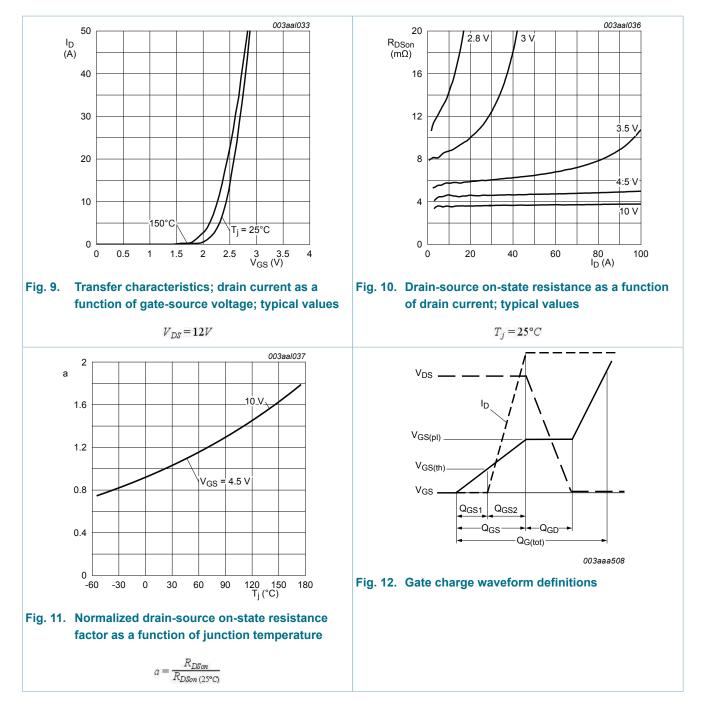
 $T_j = 25^{\circ}C$ 



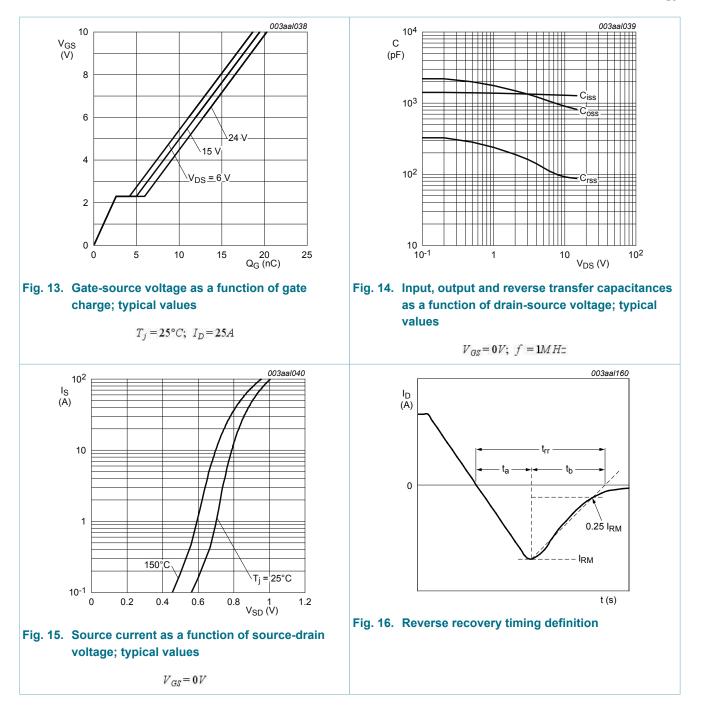
 $T_j = 25^{\circ}C; \ I_D = 25A$ 

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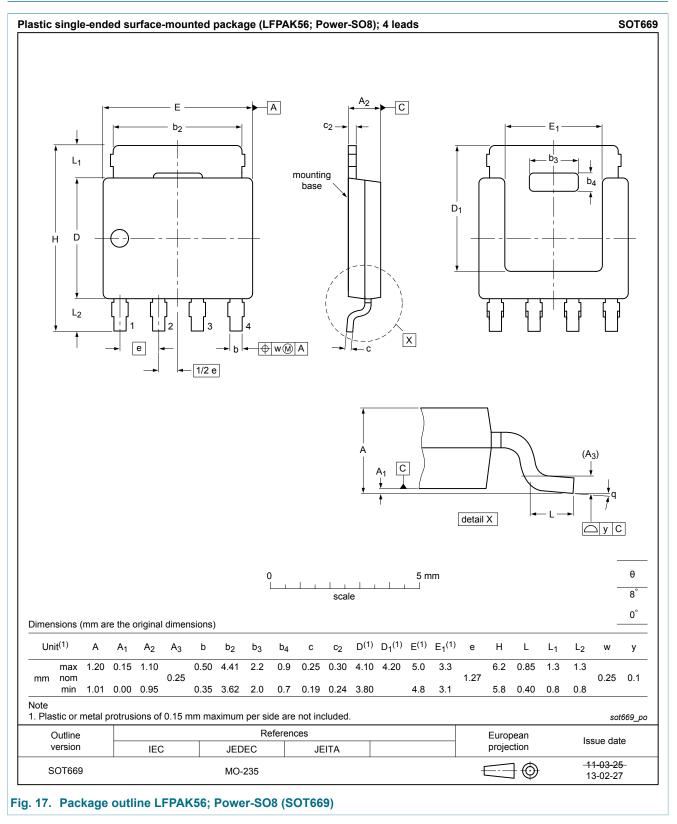


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#### N-channel 30 V, 4.0 mΩ logic level MOSFET in LFPAK56 using NextPowerS3 Technology

### **11. Package outline**



PSMN4R0-30YLD

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